

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

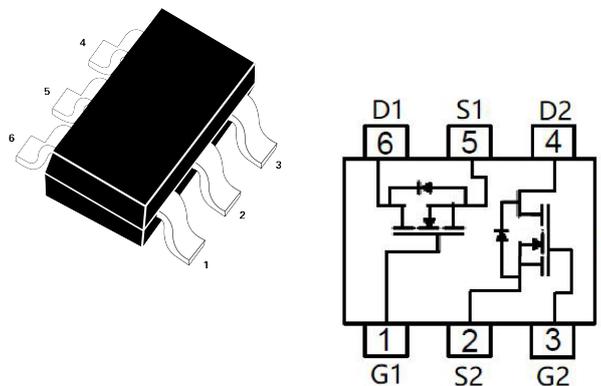


| BVDSS | RDS(ON) | ID |
|-------|---------|------|
| 30V | 29mΩ | 4.5A |

Description

The JH6800B uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

Dual SOT-23-6 Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|--------------------------|---|------------|------------|
| V_{DS} | Drain-Source Voltage | 30 | V |
| V_{GS} | Gate-Source Voltage | ± 12 | V |
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 4.5V^1$ | 4.5 | A |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 4.5V^1$ | 2.8 | A |
| I_{DM} | Pulsed Drain Current ² | 15 | A |
| $P_D @ T_A = 25^\circ C$ | Total Power Dissipation ³ | 1.25 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|--|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient ¹ | --- | 125 | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | -- | - | $^\circ C/W$ |

Electrical Characteristics (T_J=25°C unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|---|--|--|------|------|------|-------|
| Off Characteristic | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 30 | - | - | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =30V, V _{GS} =0V, | - | - | 1.0 | μA |
| I _{GSS} | Gate to Body Leakage Current | V _{DS} =0V, V _{GS} = ±20V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 1.0 | 1.5 | 2.5 | V |
| R _{DS(on)} | Static Drain-Source on-Resistance note2 | V _{GS} =10V, I _D =4A | - | 29 | 38 | mΩ |
| | | V _{GS} =4.5V, I _D =3A | - | 45 | 65 | |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, f=1.0MHz | - | 233 | - | pF |
| C _{oss} | Output Capacitance | | - | 44 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | | - | 33 | - | pF |
| Q _g | Total Gate Charge | V _{DS} =15V, I _D =2A, V _{GS} =10V | - | 3 | - | nC |
| Q _{gs} | Gate-Source Charge | | - | 0.5 | - | nC |
| Q _{gd} | Gate-Drain("Miller") Charge | | - | 0.8 | - | nC |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-on Delay Time | V _{DS} =15V, I _D =4A, R _{GEN} =3Ω, V _{GS} =10V | - | 4 | - | ns |
| t _r | Turn-on Rise Time | | - | 2.1 | - | ns |
| t _{d(off)} | Turn-off Delay Time | | - | 15 | - | ns |
| t _f | Turn-off Fall Time | | - | 3.2 | - | ns |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I _S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 4.5 | A |
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 16 | A |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} =0V, I _S =4A | - | - | 1.2 | V |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure 1: Output Characteristics

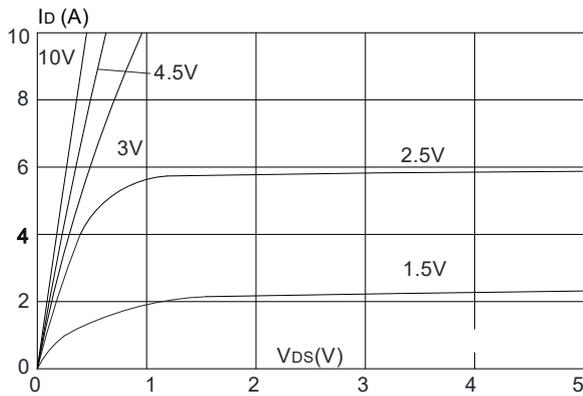


Figure 2: Typical Transfer Characteristics

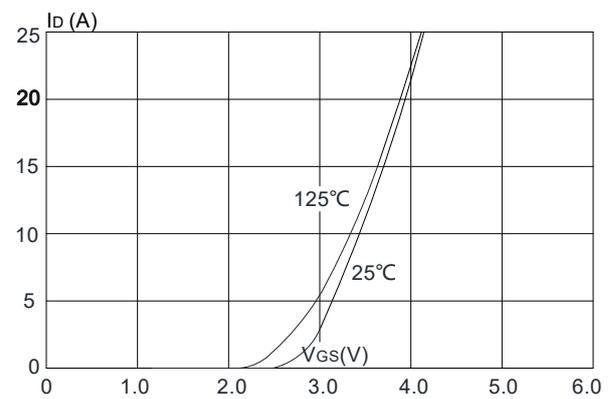


Figure 3: On-resistance vs. Drain Current

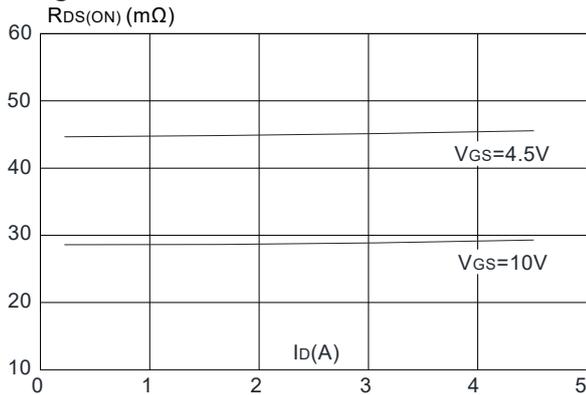


Figure 4: Body Diode Characteristics

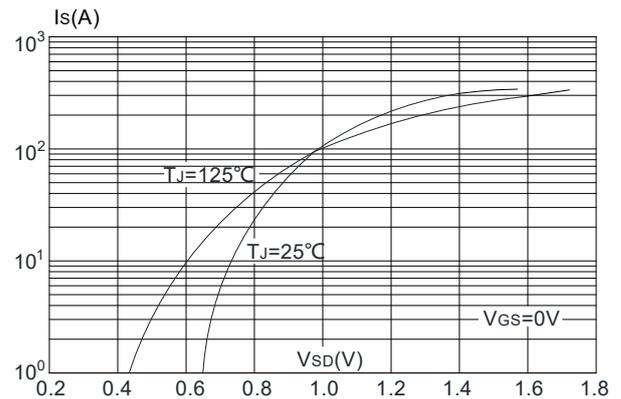


Figure 5: Gate Charge Characteristics

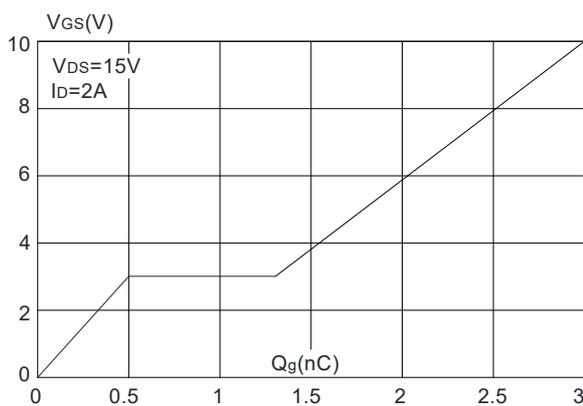


Figure 6: Capacitance Characteristics

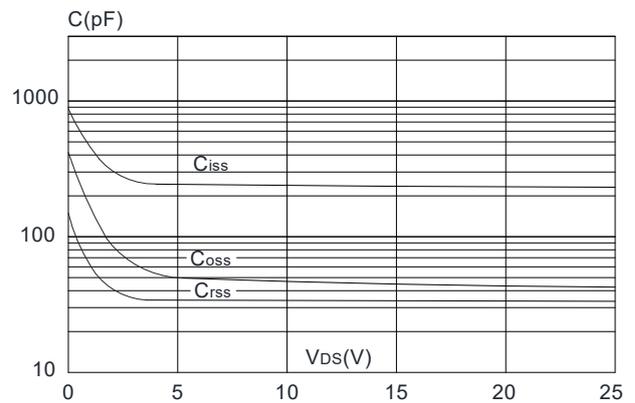


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

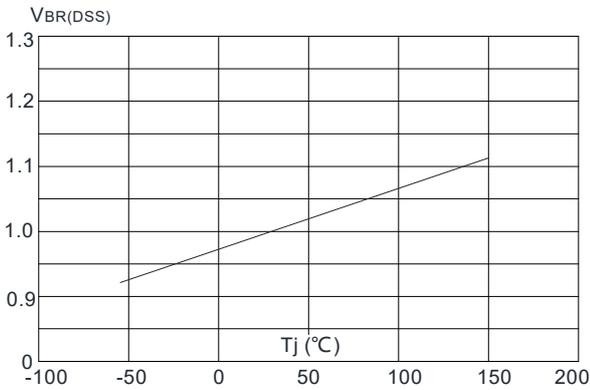


Figure 8: Normalized on Resistance vs. Junction Temperature

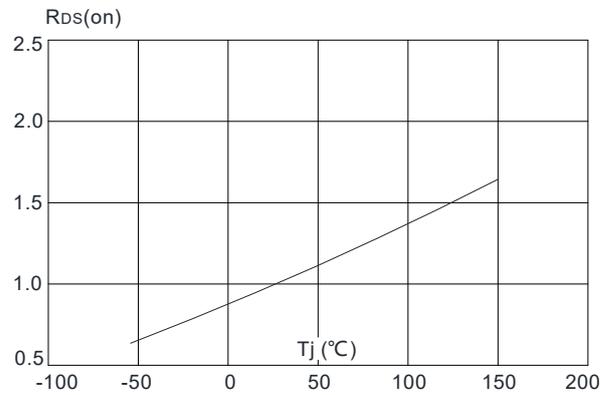


Figure 9: Maximum Safe Operating Area

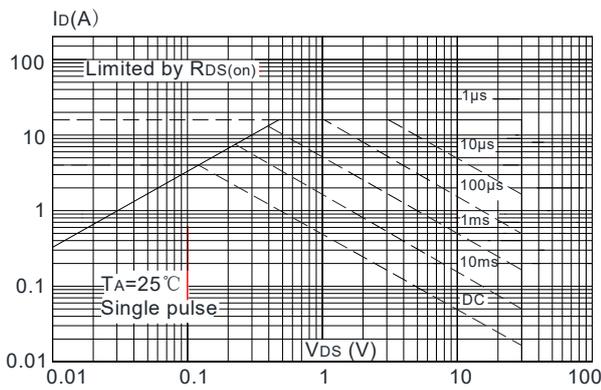


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

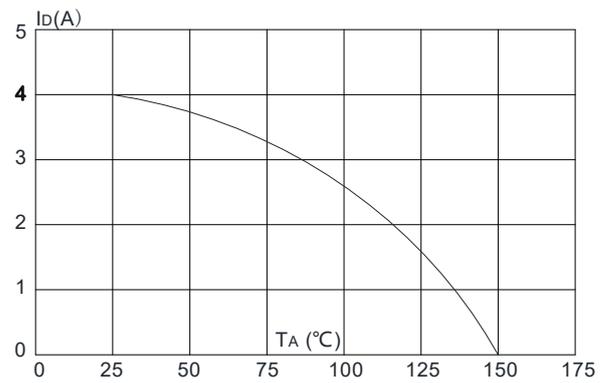
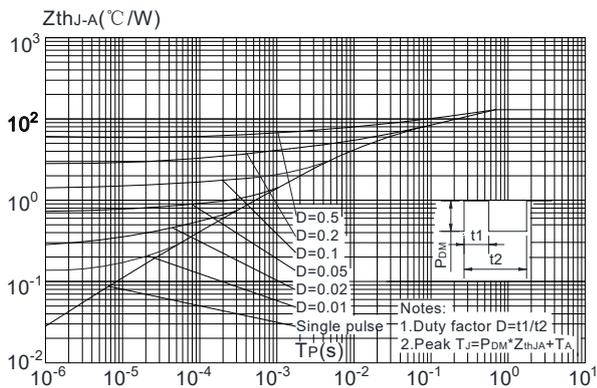
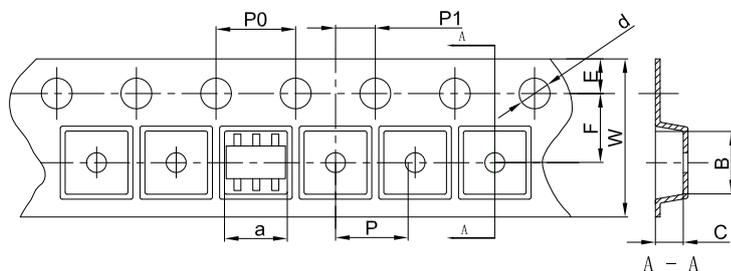


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



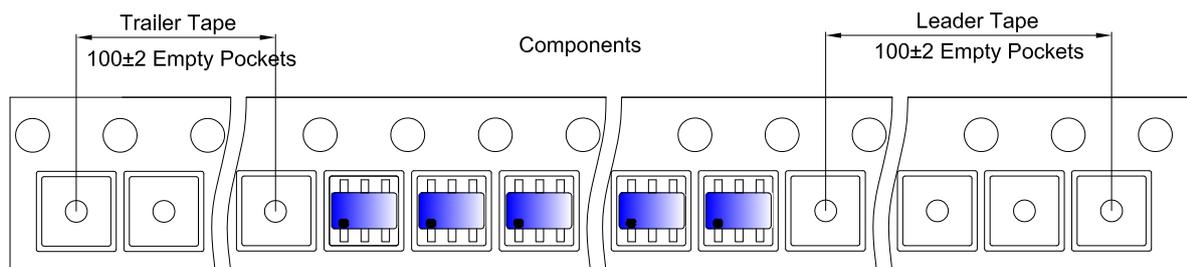
SOT-23-6L Tape and Reel

SOT-23-6L Embossed Carrier Tape

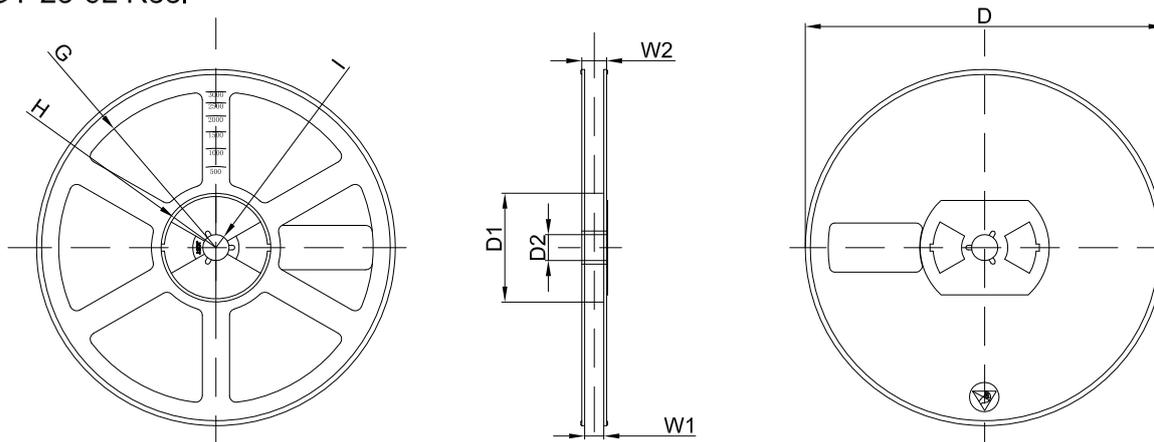


| Dimensions are in millimeter | | | | | | | | | | |
|------------------------------|------|------|------|-------|------|------|------|------|------|------|
| Pkg type | a | B | C | d | E | F | P0 | P | P1 | W |
| SOT-23-6L | 3.17 | 3.23 | 1.37 | Ø1.55 | 1.75 | 3.50 | 4.00 | 4.00 | 2.00 | 8.00 |

SOT-23-6L Tape Leader and Trailer

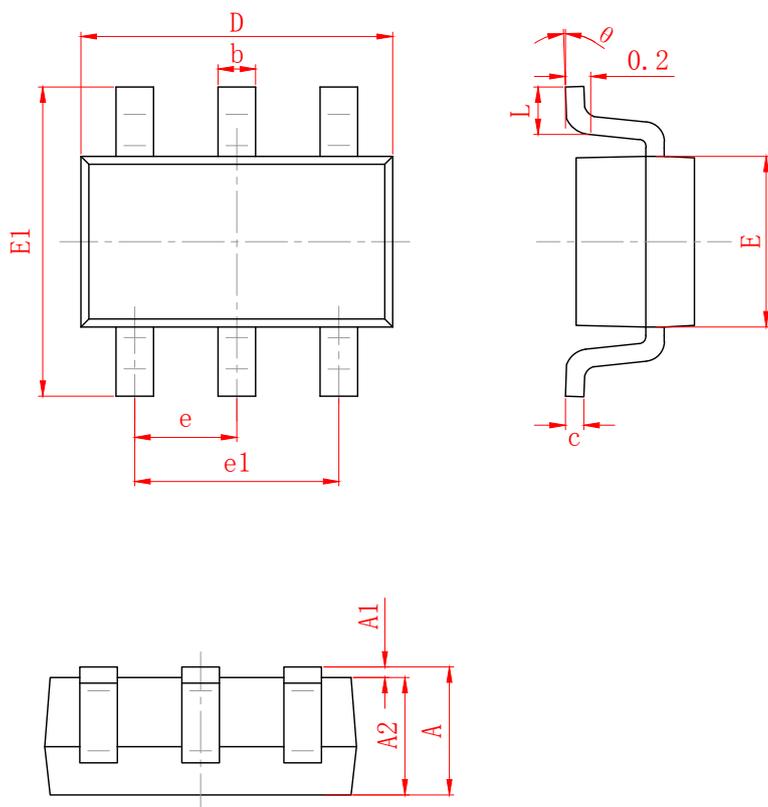


SOT-23-6L Reel



| Dimensions are in millimeter | | | | | | | | |
|------------------------------|---------|-------|-------|--------|--------|-------|------|-------|
| Reel Option | D | D1 | D2 | G | H | I | W1 | W2 |
| 7" Dia | Ø180.00 | 60.00 | 13.00 | R78.00 | R25.60 | R6.50 | 9.50 | 13.10 |

| REEL | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) | G.W.(kg) |
|----------|-----------|------------|--------------|-------------|-----------------|----------|
| 3000 pcs | 7 inch | 30,000 pcs | 203×203×195 | 120,000 pcs | 438×438×220 | |



| SYMBOL | MILLIMETER | |
|----------|-------------|-------|
| | MIN | MAX |
| A | 1.050 | 1.250 |
| A1 | 0.000 | 0.100 |
| A2 | 1.050 | 1.150 |
| b | 0.250 | 0.450 |
| c | 0.100 | 0.200 |
| D | 2.820 | 3.020 |
| E | 1.500 | 1.700 |
| E1 | 2.650 | 2.950 |
| e | 0.950 (BSC) | |
| e1 | 1.800 | 2.000 |
| L | 0.300 | 0.500 |
| θ | 0° | 8° |

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